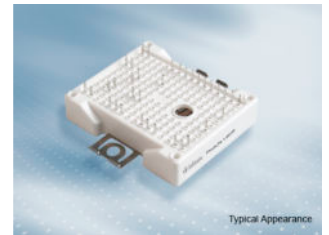


EasyPIM™ module with fast Trench/Fieldstop IGBT3 and emitter controlled 3 diode and PressFIT / NTC

Features

- Electrical features
 - $V_{CES} = 650\text{ V}$
 - $I_{C\text{ nom}} = 50\text{ A} / I_{CRM} = 100\text{ A}$
 - Trench IGBT 3
 - Low switching losses
- Mechanical features
 - Al_2O_3 substrate with low thermal resistance
 - Compact design
 - PressFIT contact technology
 - Rugged mounting due to integrated mounting clamps



Potential applications

- Air conditioning

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description

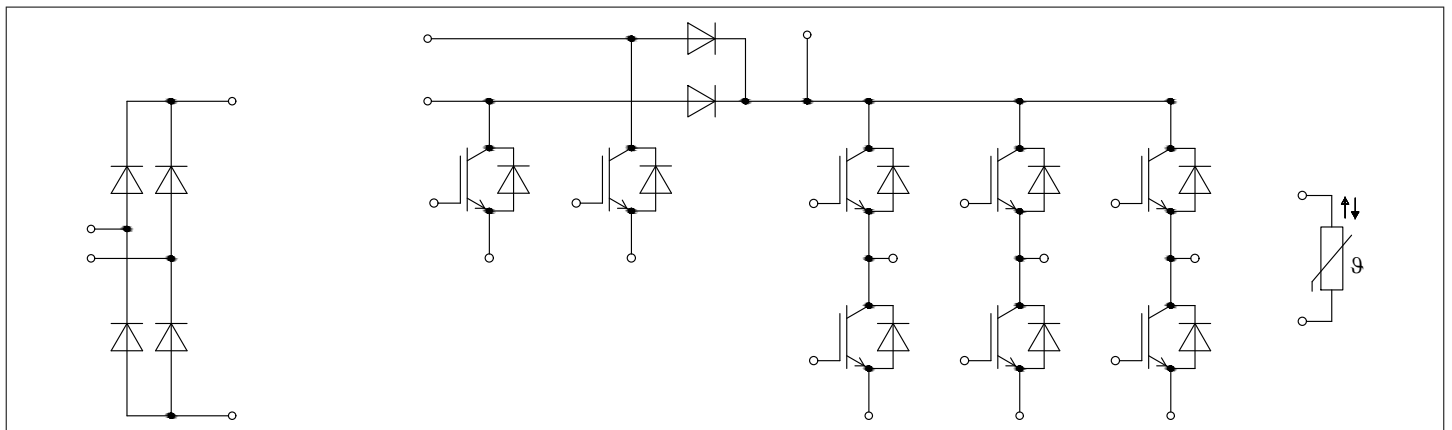


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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50 \text{ Hz}$, $t = 1 \text{ min}$	2.5	kV
Internal isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Creepage distance	d_{Creep}	terminal to heatsink	11.5	mm
Creepage distance	d_{Creep}	terminal to terminal	6.3	mm
Clearance	d_{Clear}	terminal to heatsink	10.0	mm
Clearance	d_{Clear}	terminal to terminal	5.0	mm
Comparative tracking index	CTI		> 200	
Relative thermal index (electrical)	RTI	housing	140	°C

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	L_{SCE}			30		nH
Module lead resistance, terminals - chip	$R_{AA'+CC'}$	$T_H = 25^\circ\text{C}$, per switch		6		mΩ
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_H = 25^\circ\text{C}$, per switch		5		mΩ
Storage temperature	T_{stg}		-40		125	°C
Mounting force per clamp	F		40		80	N
Weight	G			39		g

Note: The current under continuous operation is limited to 25 A rms per connector pin.

2 IGBT, Inverter

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CES}		$T_{vj} = 25^\circ\text{C}$	650	V
Implemented collector current	I_{CN}			50	A
Continuous DC collector current	I_{CDC}	$T_{vj \text{ max}} = 175^\circ\text{C}$	$T_H = 65^\circ\text{C}$	45	A
Repetitive peak collector current	I_{CRM}	t_p limited by $T_{vj \text{ op}}$		100	A

(table continues...)

Table 3 (continued) Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Gate-emitter peak voltage	V_{GES}		± 20	V

Table 4 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 50\ A, V_{GE} = 15\ V$	$T_{vj} = 25\ ^\circ C$	1.45	1.90	V
			$T_{vj} = 125\ ^\circ C$	1.60		
			$T_{vj} = 150\ ^\circ C$	1.70		
Gate threshold voltage	V_{GEth}	$I_C = 0.8\ mA, V_{CE} = V_{GE}, T_{vj} = 25\ ^\circ C$	5.05	5.80	6.45	V
Gate charge	Q_G	$V_{GE} = \pm 15\ V, V_{CC} = 400\ V$		0.5		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\ ^\circ C$		0		Ω
Input capacitance	C_{ies}	$f = 1000\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$		3.1		nF
Reverse transfer capacitance	C_{res}	$f = 1000\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$		0.095		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 650\ V, V_{GE} = 0\ V$	$T_{vj} = 25\ ^\circ C$		0.018	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\ V, V_{GE} = 20\ V, T_{vj} = 25\ ^\circ C$			100	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 50\ A, V_{CC} = 300\ V, V_{GE} = \pm 15\ V, R_{Gon} = 8.2\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.029		μs
			$T_{vj} = 125\ ^\circ C$	0.030		
			$T_{vj} = 150\ ^\circ C$	0.031		
Rise time (inductive load)	t_r	$I_C = 50\ A, V_{CC} = 300\ V, V_{GE} = \pm 15\ V, R_{Gon} = 8.2\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.059		μs
			$T_{vj} = 125\ ^\circ C$	0.060		
			$T_{vj} = 150\ ^\circ C$	0.061		
Turn-off delay time (inductive load)	t_{doff}	$I_C = 50\ A, V_{CC} = 300\ V, V_{GE} = \pm 15\ V, R_{Goff} = 8.2\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.180		μs
			$T_{vj} = 125\ ^\circ C$	0.210		
			$T_{vj} = 150\ ^\circ C$	0.220		
Fall time (inductive load)	t_f	$I_C = 50\ A, V_{CC} = 300\ V, V_{GE} = \pm 15\ V, R_{Goff} = 8.2\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.110		μs
			$T_{vj} = 125\ ^\circ C$	0.140		
			$T_{vj} = 150\ ^\circ C$	0.150		
Turn-on energy loss per pulse	E_{on}	$I_C = 50\ A, V_{CC} = 300\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Gon} = 8.2\ \Omega, di/dt = 550\ A/\mu s (T_{vj} = 150\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$	1.37		mJ
			$T_{vj} = 125\ ^\circ C$	1.78		
			$T_{vj} = 150\ ^\circ C$	1.89		

(table continues...)

Table 4 (continued) **Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Turn-off energy loss per pulse	E_{off}	$I_C = 50\text{ A}$, $V_{CC} = 300\text{ V}$, $L_\sigma = 35\text{ nH}$, $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 8.2\ \Omega$, $dv/dt = 4000\text{ V}/\mu\text{s}$ ($T_{vj} = 150\text{ °C}$)	$T_{vj} = 25\text{ °C}$	1.17		mJ
			$T_{vj} = 125\text{ °C}$	1.57		
			$T_{vj} = 150\text{ °C}$	1.66		
SC data	I_{SC}	$V_{GE} \leq 15\text{ V}$, $V_{CC} = 360\text{ V}$, $V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$	$t_p \leq 6\ \mu\text{s}$, $T_{vj} = 150\text{ °C}$	250		A
Thermal resistance, junction to heat sink	R_{thJH}	per IGBT		1.02		K/W
Temperature under switching conditions	$T_{vj\ op}$		-40		150	°C

3 Diode, Inverter

Table 5 **Maximum rated values**

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		$T_{vj} = 25\text{ }^{\circ}\text{C}$	650	V
Continuous DC forward current	I_F			50	A
Repetitive peak forward current	I_{FRM}	$t_P = 1\text{ ms}$		100	A
I^2t - value	I^2t	$t_P = 10\text{ ms}$, $V_R = 0\text{ V}$	$T_{vj} = 125\text{ }^{\circ}\text{C}$	370	A^2s
			$T_{vj} = 150\text{ }^{\circ}\text{C}$	330	

Table 6 **Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 50\text{ A}$, $V_{GE} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$	1.56	1.95	V
			$T_{vj} = 125\text{ °C}$	1.49		
			$T_{vj} = 150\text{ °C}$	1.45		
Peak reverse recovery current	I_{RM}	$V_{CC} = 300\text{ V}$, $I_F = 50\text{ A}$, $V_{GE} = -15\text{ V}$, $-di_F/dt = 550\text{ A}/\mu\text{s}$ ($T_{vj} = 150\text{ °C}$)	$T_{vj} = 25\text{ °C}$	34		A
			$T_{vj} = 125\text{ °C}$	48		
			$T_{vj} = 150\text{ °C}$	53		
Recovered charge	Q_r	$V_{CC} = 300\text{ V}$, $I_F = 50\text{ A}$, $V_{GE} = -15\text{ V}$, $-di_F/dt = 550\text{ A}/\mu\text{s}$ ($T_{vj} = 150\text{ °C}$)	$T_{vj} = 25\text{ °C}$	2.4		μC
			$T_{vj} = 125\text{ °C}$	4.4		
			$T_{vj} = 150\text{ °C}$	5.1		

(table continues...)

Table 6 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Reverse recovery energy	E_{rec}	$V_{CC} = 300\text{ V}$, $I_F = 50\text{ A}$, $V_{GE} = -15\text{ V}$, $-di_F/dt = 550\text{ A}/\mu\text{s}$ ($T_{vj} = 150\text{ °C}$)	$T_{vj} = 25\text{ °C}$	0.62		mJ
			$T_{vj} = 125\text{ °C}$	1.11		
			$T_{vj} = 150\text{ °C}$	1.28		
Thermal resistance, junction to heat sink	R_{thJH}	per diode		1.45		K/W
Temperature under switching conditions	$T_{vj,op}$		-40		150	°C

4 Diode, Rectifier

Table 7 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		$T_{vj} = 25\text{ °C}$	1600	V
Maximum RMS forward current per chip	I_{FRMSM}	$T_H = 80\text{ °C}$		50	A
Maximum RMS current at rectifier output	I_{RMSM}	$T_H = 80\text{ °C}$		50	A
Surge forward current	I_{FSM}	$t_P = 10\text{ ms}$	$T_{vj} = 25\text{ °C}$	665	A
			$T_{vj} = 150\text{ °C}$	526	
I^2t - value	I^2t	$t_P = 10\text{ ms}$	$T_{vj} = 25\text{ °C}$	2210	A ² s
			$T_{vj} = 150\text{ °C}$	1380	

Table 8 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 50\text{ A}$, $T_{vj} = 150\text{ °C}$		0.93		V
Reverse current	I_r	$T_{vj} = 150\text{ °C}$, $V_R = 1600\text{ V}$		1.1		mA
Thermal resistance, junction to heat sink	R_{thJH}	per diode		1.03		K/W
Temperature under switching conditions	$T_{vj,op}$		-40		150	°C

5 IGBT, Boost

Table 9 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CES}		$T_{vj} = 25\text{ °C}$	650	V
Implemented collector current	I_{CN}			50	A
Continuous DC collector current	I_{CDC}	$T_{vj\text{ max}} = 175\text{ °C}$	$T_H = 65\text{ °C}$	35	A
Repetitive peak collector current	I_{CRM}	t_p limited by $T_{vj\text{ op}}$		100	A
Gate-emitter peak voltage	V_{GES}			± 20	V

Table 10 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\text{ sat}}$	$I_C = 50\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25\text{ °C}$		1.60	2.20	V
			$T_{vj} = 125\text{ °C}$		1.75		
			$T_{vj} = 150\text{ °C}$		1.79		
Gate threshold voltage	V_{GEth}	$I_C = 0.5\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25\text{ °C}$		3.85	4.60	5.35	V
Gate charge	Q_G	$V_{GE} = \pm 15\text{ V}, V_{CC} = 400\text{ V}$			0.217		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\text{ °C}$			0		Ω
Input capacitance	C_{ies}	$f = 1000\text{ kHz}, T_{vj} = 25\text{ °C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$			2.75		nF
Reverse transfer capacitance	C_{res}	$f = 1000\text{ kHz}, T_{vj} = 25\text{ °C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$			0.01		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 650\text{ V}, V_{GE} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$			0.014	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25\text{ °C}$				100	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 50\text{ A}, V_{CC} = 300\text{ V}, V_{GE} = \pm 15\text{ V}, R_{Gon} = 18\text{ }\Omega$	$T_{vj} = 25\text{ °C}$		0.054		μs
			$T_{vj} = 125\text{ °C}$		0.051		
			$T_{vj} = 150\text{ °C}$		0.050		
Rise time (inductive load)	t_r	$I_C = 50\text{ A}, V_{CC} = 300\text{ V}, V_{GE} = \pm 15\text{ V}, R_{Gon} = 18\text{ }\Omega$	$T_{vj} = 25\text{ °C}$		0.064		μs
			$T_{vj} = 125\text{ °C}$		0.064		
			$T_{vj} = 150\text{ °C}$		0.065		
Turn-off delay time (inductive load)	t_{doff}	$I_C = 50\text{ A}, V_{CC} = 300\text{ V}, V_{GE} = \pm 15\text{ V}, R_{Goff} = 18\text{ }\Omega$	$T_{vj} = 25\text{ °C}$		0.130		μs
			$T_{vj} = 125\text{ °C}$		0.140		
			$T_{vj} = 150\text{ °C}$		0.150		

(table continues...)

Table 10 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Fall time (inductive load)	t_f	$I_C = 50 \text{ A}$, $V_{CC} = 300 \text{ V}$, $V_{GE} = \pm 15 \text{ V}$, $R_{Goff} = 18 \Omega$	$T_{vj} = 25 \text{ °C}$	0.016		μs
			$T_{vj} = 125 \text{ °C}$	0.027		
			$T_{vj} = 150 \text{ °C}$	0.029		
Turn-on energy loss per pulse	E_{on}	$I_C = 50 \text{ A}$, $V_{CC} = 300 \text{ V}$, $L_\sigma = 35 \text{ nH}$, $V_{GE} = \pm 15 \text{ V}$, $R_{Gon} = 18 \Omega$, $di/dt = 650 \text{ A}/\mu\text{s}$ ($T_{vj} = 150 \text{ °C}$)	$T_{vj} = 25 \text{ °C}$	1.52		mJ
			$T_{vj} = 125 \text{ °C}$	1.79		
			$T_{vj} = 150 \text{ °C}$	1.84		
Turn-off energy loss per pulse	E_{off}	$I_C = 50 \text{ A}$, $V_{CC} = 300 \text{ V}$, $L_\sigma = 35 \text{ nH}$, $V_{GE} = \pm 15 \text{ V}$, $R_{Goff} = 18 \Omega$, $dv/dt = 1100 \text{ V}/\mu\text{s}$ ($T_{vj} = 150 \text{ °C}$)	$T_{vj} = 25 \text{ °C}$	0.41		mJ
			$T_{vj} = 125 \text{ °C}$	0.54		
			$T_{vj} = 150 \text{ °C}$	0.57		
SC data	I_{SC}	$V_{GE} \leq 15 \text{ V}$, $V_{CC} = 400 \text{ V}$, $V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$	$t_p \leq 0 \mu\text{s}$, $T_{vj} = 150 \text{ °C}$	250		A
Thermal resistance, junction to heat sink	R_{thJH}	per IGBT		1.42		K/W
Temperature under switching conditions	$T_{vj op}$		-40		150	°C

6 Diode, Boost

Table 11 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		$T_{vj} = 25 \text{ °C}$	650	V
Implemented forward current	I_{FN}			50	A
Continuous DC forward current	I_F			50	A
Repetitive peak forward current	I_{FRM}	$t_p = 1 \text{ ms}$		100	A
I^2t - value	I^2t	$t_p = 10 \text{ ms}$, $V_R = 0 \text{ V}$	$T_{vj} = 125 \text{ °C}$	225	A^2s
			$T_{vj} = 150 \text{ °C}$	215	

Table 12 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 50 \text{ A}$, $V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ °C}$	1.65	2.15	V
			$T_{vj} = 125 \text{ °C}$	1.55		
			$T_{vj} = 150 \text{ °C}$	1.50		
Peak reverse recovery current	I_{RM}	$V_{CC} = 300 \text{ V}$, $I_F = 50 \text{ A}$, $V_{GE} = 15 \text{ V}$, $-di_F/dt = 650 \text{ A}/\mu\text{s}$ ($T_{vj} = 150 \text{ °C}$)	$T_{vj} = 25 \text{ °C}$	14.9		A
			$T_{vj} = 125 \text{ °C}$	24.5		
			$T_{vj} = 150 \text{ °C}$	26.5		
Recovered charge	Q_r	$V_{CC} = 300 \text{ V}$, $I_F = 50 \text{ A}$, $V_{GE} = 15 \text{ V}$, $-di_F/dt = 650 \text{ A}/\mu\text{s}$ ($T_{vj} = 150 \text{ °C}$)	$T_{vj} = 25 \text{ °C}$	1.1		μC
			$T_{vj} = 125 \text{ °C}$	2.2		
			$T_{vj} = 150 \text{ °C}$	2.6		
Reverse recovery energy	E_{rec}	$V_{CC} = 300 \text{ V}$, $I_F = 50 \text{ A}$, $V_{GE} = 15 \text{ V}$, $-di_F/dt = 650 \text{ A}/\mu\text{s}$ ($T_{vj} = 150 \text{ °C}$)	$T_{vj} = 25 \text{ °C}$	0.18		mJ
			$T_{vj} = 125 \text{ °C}$	0.38		
			$T_{vj} = 150 \text{ °C}$	0.46		
Thermal resistance, junction to heat sink	R_{thJH}	per diode		1.61		K/W
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		150	°C

7 Diode, Reverse

Table 13 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} = 25 \text{ °C}$	650	V
Continuous DC forward current	I_F		10	A
Repetitive peak forward current	I_{FRM}	$t_p = 1 \text{ ms}$	20	A
I^2t - value	I^2t	$t_p = 10 \text{ ms}$, $V_R = 0 \text{ V}$	$T_{vj} = 125 \text{ °C}$	A^2s
			$T_{vj} = 150 \text{ °C}$	

Table 14 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 10 \text{ A}$, $V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ °C}$		1.60	2.00	V
			$T_{vj} = 125 \text{ °C}$		1.55		
			$T_{vj} = 150 \text{ °C}$		1.52		
Thermal resistance, junction to heat sink	R_{thJH}	per diode			2.72		K/W
Temperature under switching conditions	$T_{vj op}$			-40		150	°C

8 NTC-Thermistor

Table 15 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	$T_{NTC} = 25 \text{ °C}$		5		kΩ
Deviation of R_{100}	$\Delta R/R$	$T_{NTC} = 100 \text{ °C}$, $R_{100} = 493 \text{ Ω}$	-5		5	%
Power dissipation	P_{25}	$T_{NTC} = 25 \text{ °C}$			20	mW
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2 - 1/(298,15 \text{ K}))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2 - 1/(298,15 \text{ K}))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2 - 1/(298,15 \text{ K}))]$		3433		K

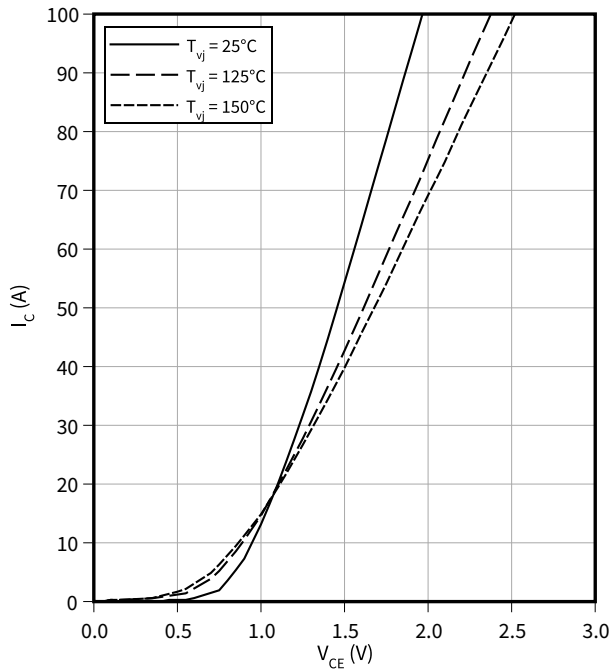
Note: Specification according to the valid application note.

9 Characteristics diagrams

Output characteristic (typical), IGBT, Inverter

$I_C = f(V_{CE})$

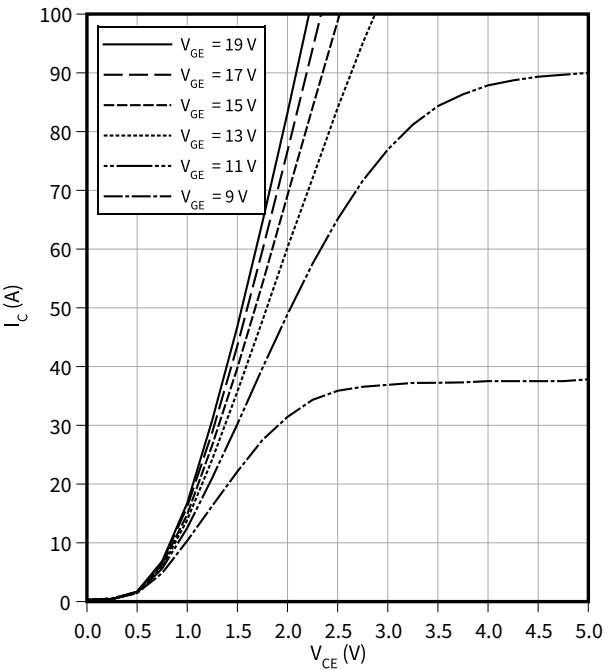
$V_{GE} = 15\text{ V}$



Output characteristic field (typical), IGBT, Inverter

$I_C = f(V_{CE})$

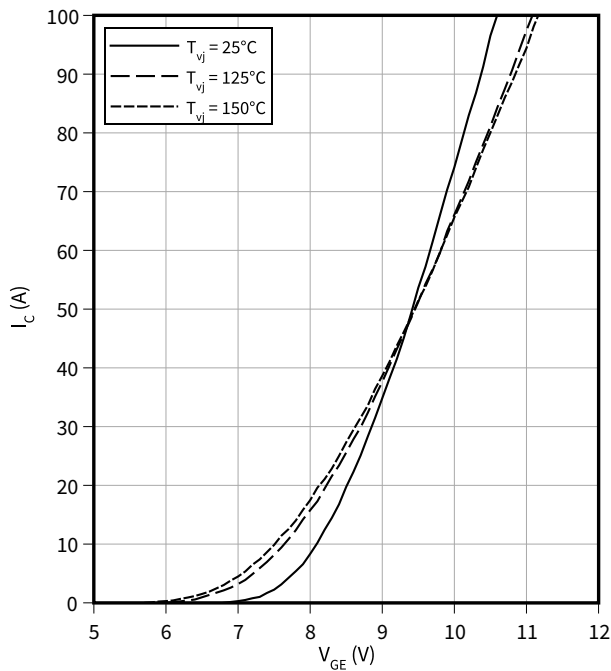
$T_{vj} = 150^\circ\text{C}$



Transfer characteristic (typical), IGBT, Inverter

$I_C = f(V_{GE})$

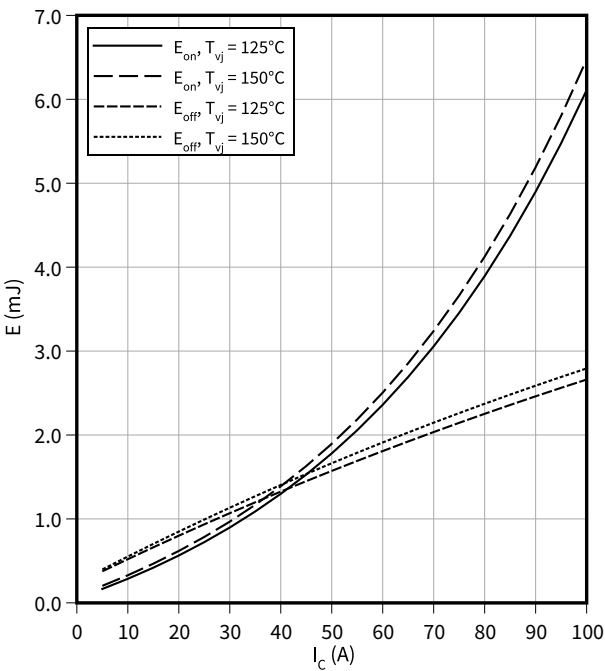
$V_{CE} = 20\text{ V}$



Switching losses (typical), IGBT, Inverter

$E = f(I_C)$

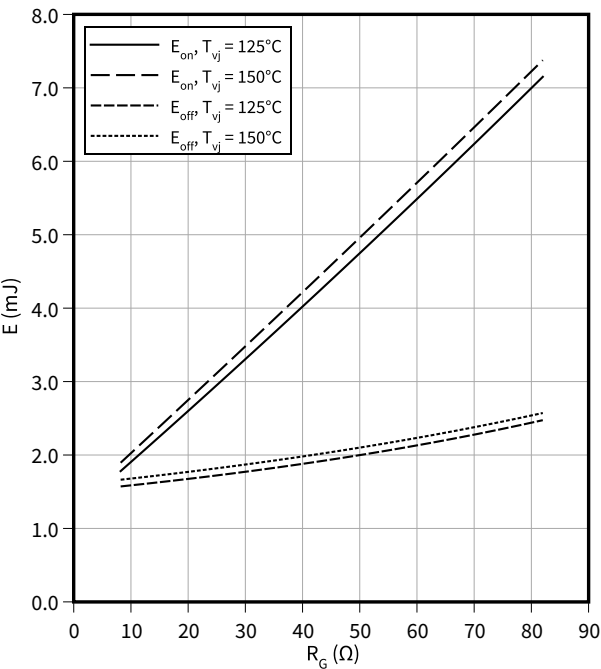
$R_{Goff} = 8.2\ \Omega$, $R_{Gon} = 8.2\ \Omega$, $V_{CC} = 300\text{ V}$, $V_{GE} = \pm 15\text{ V}$



9 Characteristics diagrams

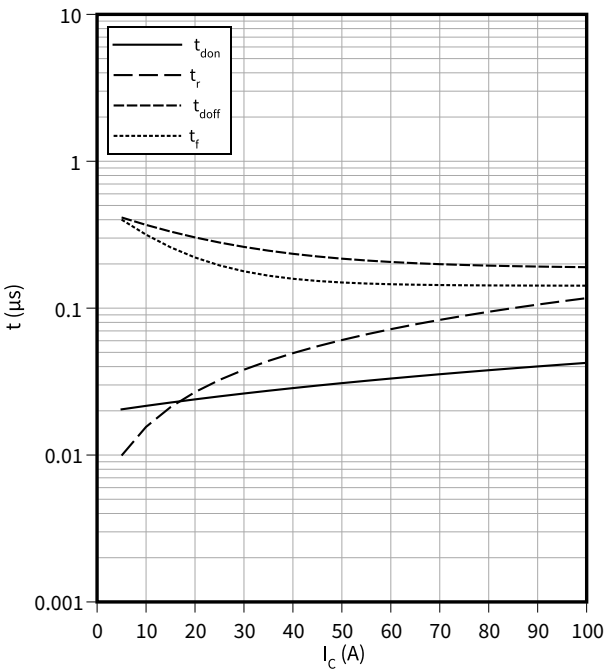
Switching losses (typical), IGBT, Inverter

$E = f(R_G)$
 $V_{GE} = \pm 15\text{ V}$, $I_C = 50\text{ A}$, $V_{CC} = 300\text{ V}$



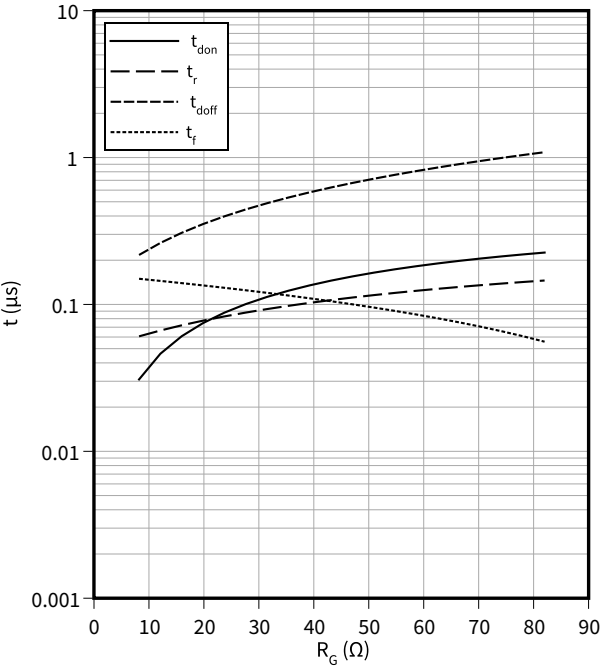
Switching times (typical), IGBT, Inverter

$t = f(I_C)$
 $R_{Goff} = 8.2\ \Omega$, $R_{Gon} = 8.2\ \Omega$, $V_{CC} = 300\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $T_{vj} = 150\text{ °C}$



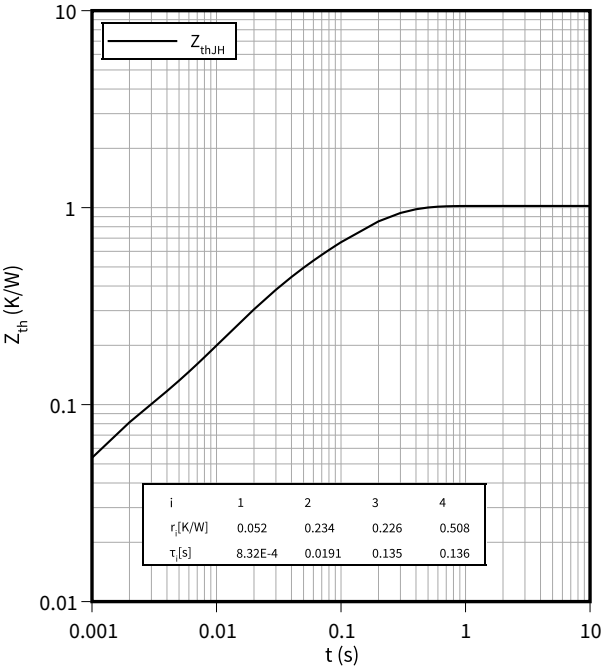
Switching times (typical), IGBT, Inverter

$t = f(R_G)$
 $I_C = 50\text{ A}$, $V_{CC} = 300\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $T_{vj} = 150\text{ °C}$



Transient thermal impedance , IGBT, Inverter

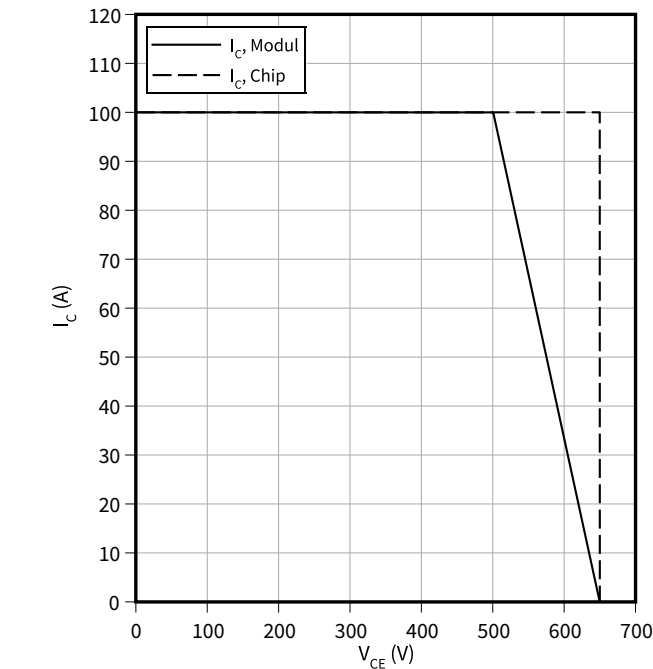
$Z_{th} = f(t)$



9 Characteristics diagrams

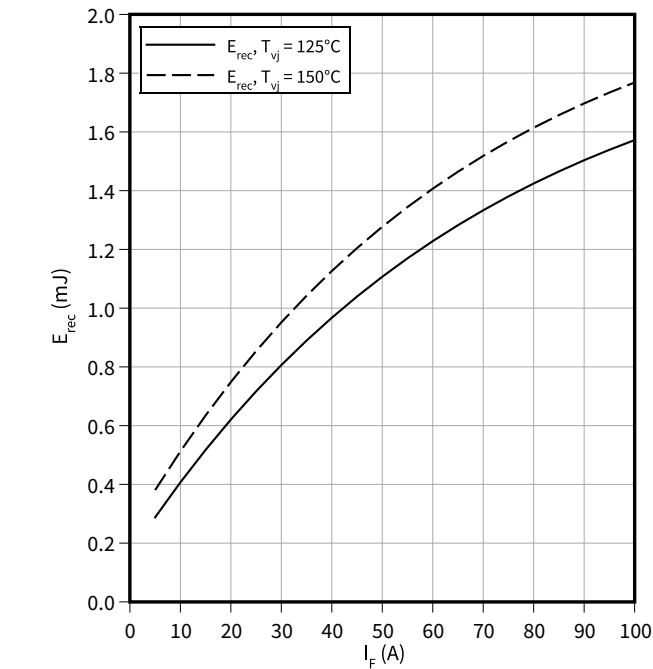
Reverse bias safe operating area (RBSOA), IGBT, Inverter

$I_C = f(V_{CE})$
 $R_{Goff} = 8.2 \Omega$, $V_{GE} = \pm 15 \text{ V}$, $T_{vj} = 150 \text{ }^\circ\text{C}$



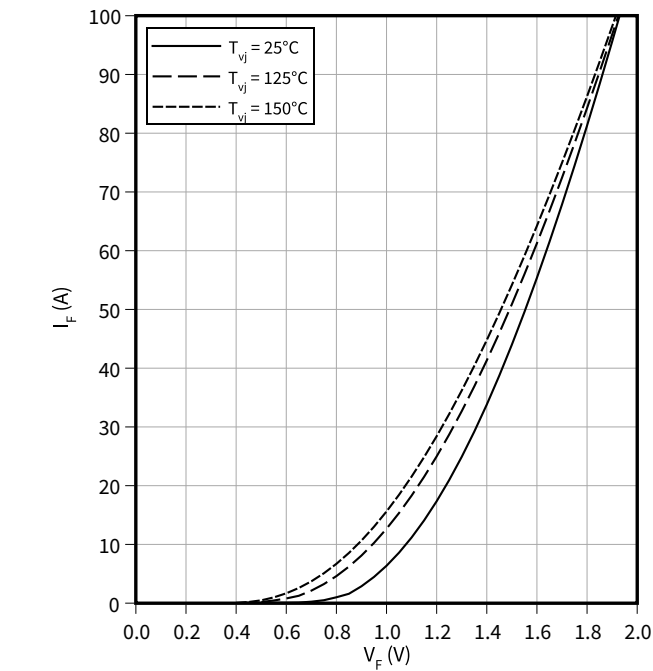
Switching losses (typical), Diode, Inverter

$E_{rec} = f(I_F)$
 $R_{Gon} = R_{Gon}(\text{IGBT})$, $V_{CC} = 300 \text{ V}$



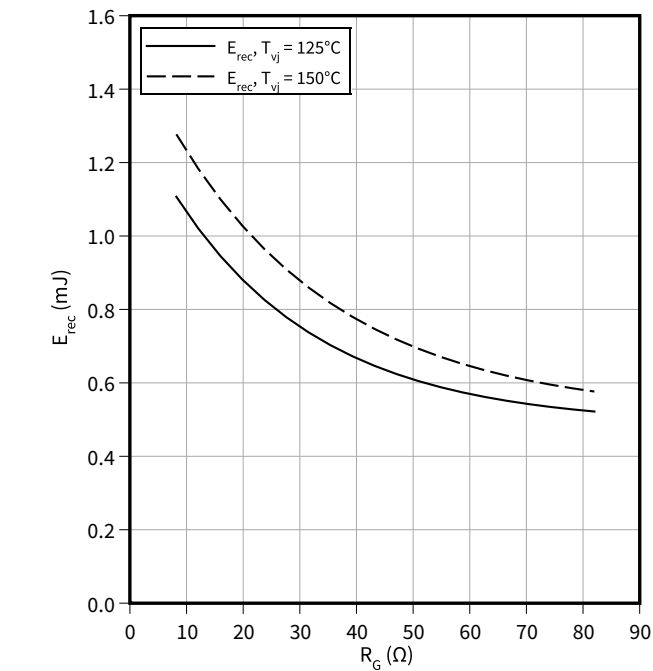
Forward characteristic (typical), Diode, Inverter

$I_F = f(V_F)$



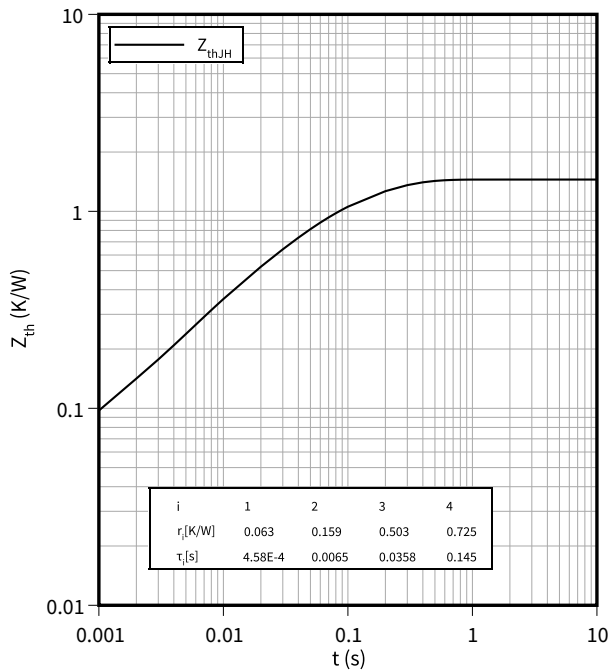
Switching losses (typical), Diode, Inverter

$E_{rec} = f(R_G)$
 $I_F = 50 \text{ A}$, $V_{CC} = 300 \text{ V}$



Transient thermal impedance, Diode, Inverter

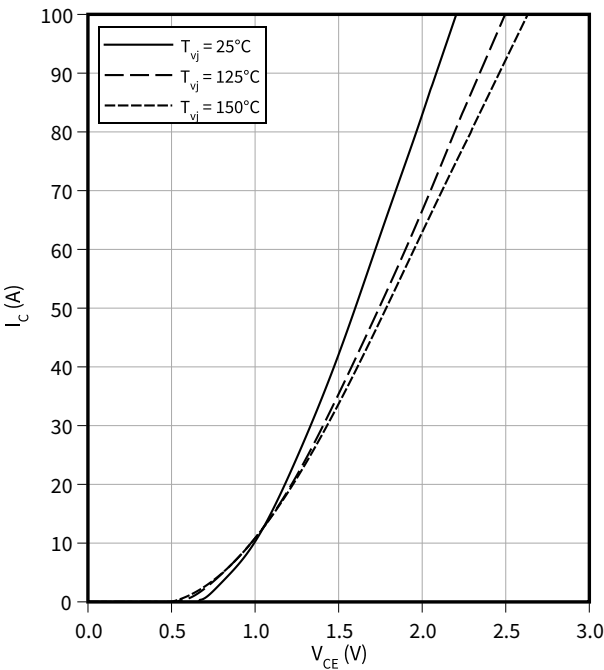
$Z_{th} = f(t)$



Output characteristic (typical), IGBT, Boost

$I_C = f(V_{CE})$

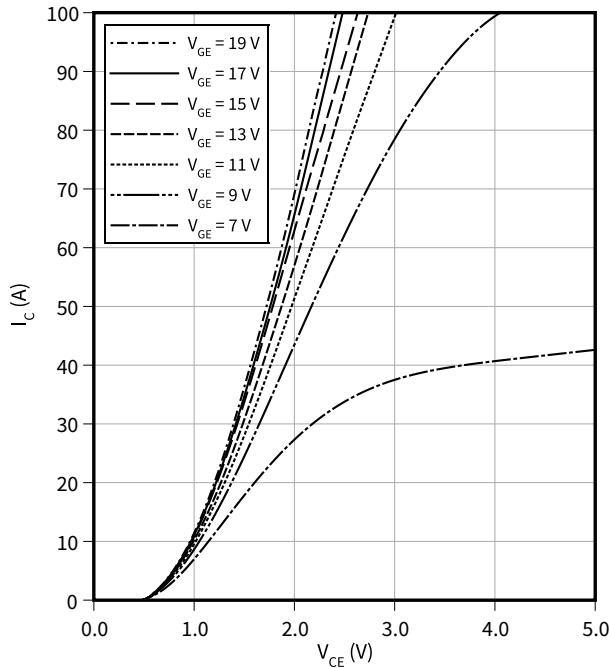
$V_{GE} = 15\text{ V}$



Output characteristic field (typical), IGBT, Boost

$I_C = f(V_{CE})$

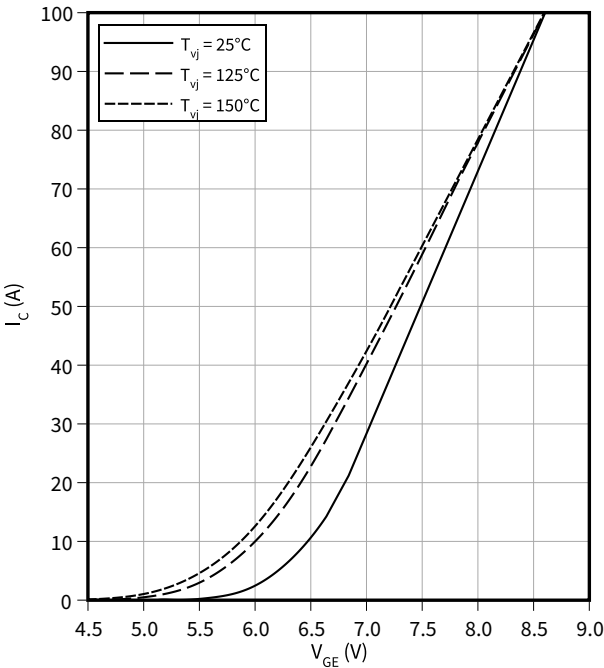
$T_{vj} = 150\text{ °C}$



Transfer characteristic (typical), IGBT, Boost

$I_C = f(V_{GE})$

$V_{CE} = 20\text{ V}$

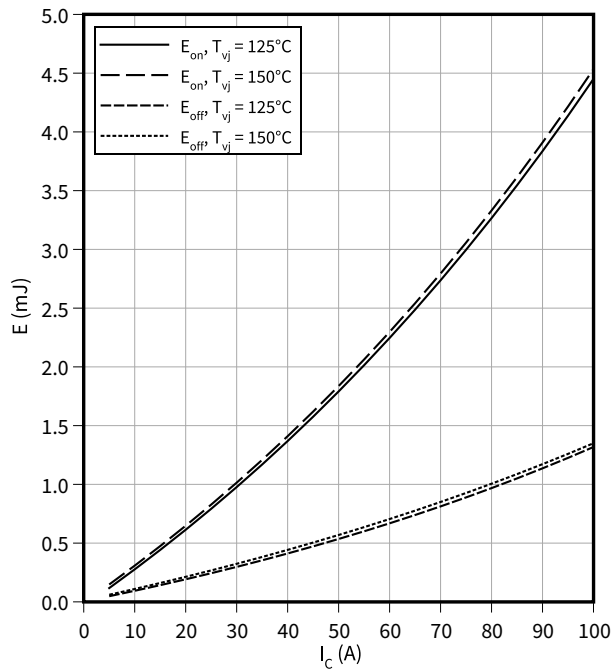


9 Characteristics diagrams

Switching losses (typical), IGBT, Boost

$E = f(I_C)$

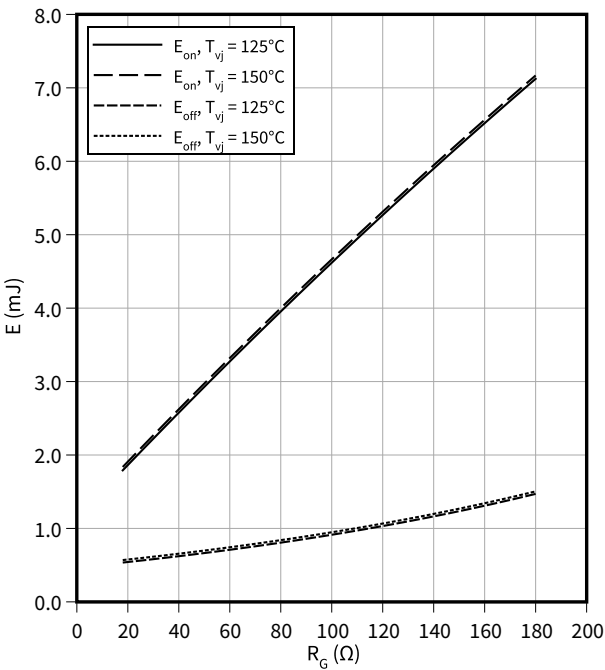
$R_{Goff} = 18 \Omega$, $R_{Gon} = 18 \Omega$, $V_{CC} = 300 \text{ V}$, $V_{GE} = \pm 15 \text{ V}$



Switching losses (typical), IGBT, Boost

$E = f(R_G)$

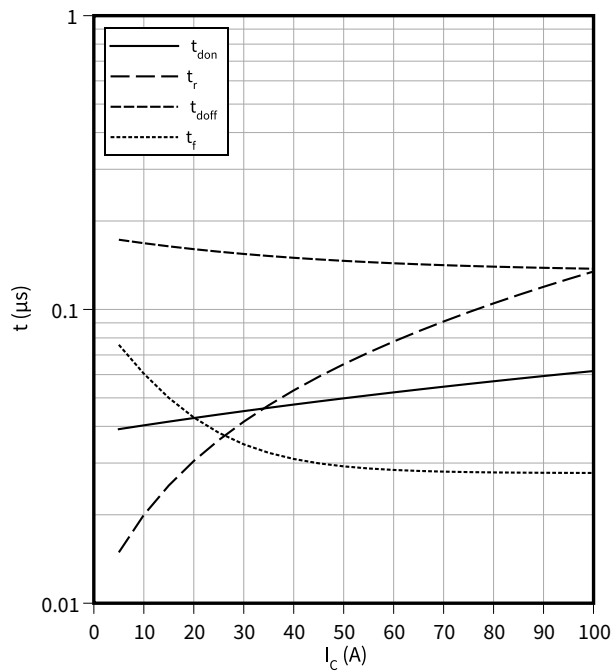
$V_{GE} = \pm 15 \text{ V}$, $V_{CC} = 300 \text{ V}$, $I_C = 50 \text{ A}$



Switching times (typical), IGBT, Boost

$t = f(I_C)$

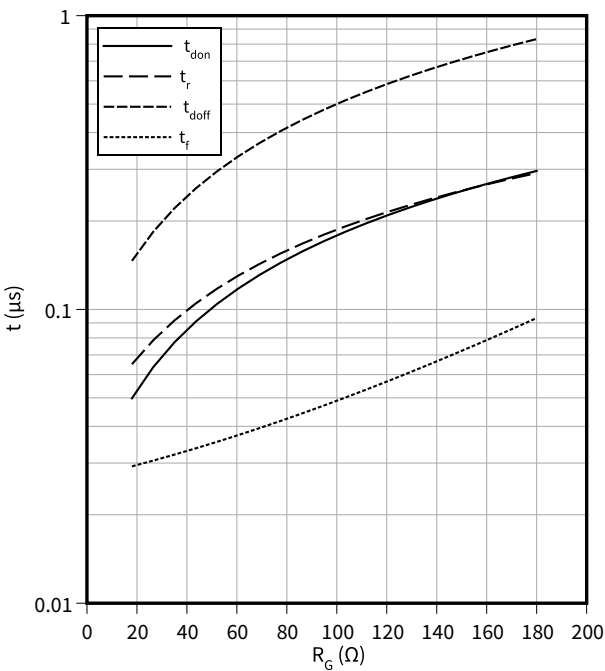
$R_{Goff} = 18 \Omega$, $R_{Gon} = 18 \Omega$, $V_{CC} = 300 \text{ V}$, $V_{GE} = \pm 15 \text{ V}$, $T_{vj} = 150 \text{ °C}$



Switching times (typical), IGBT, Boost

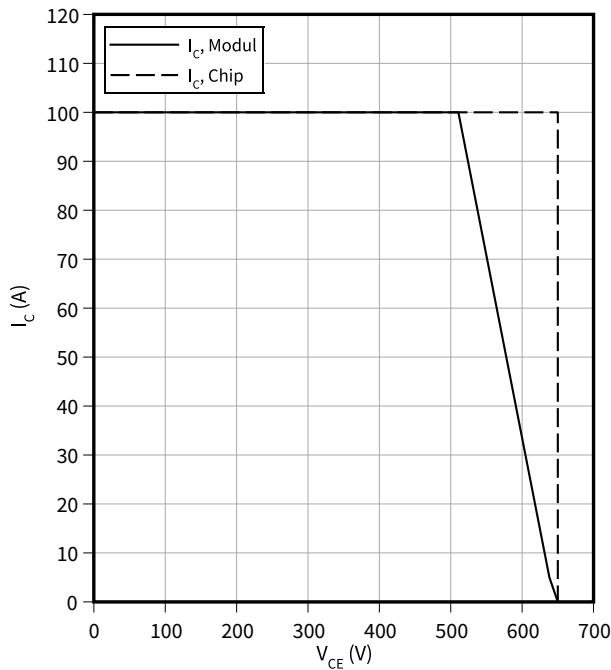
$t = f(R_G)$

$I_C = 50 \text{ A}$, $V_{CC} = 300 \text{ V}$, $V_{GE} = \pm 15 \text{ V}$, $T_{vj} = 150 \text{ °C}$



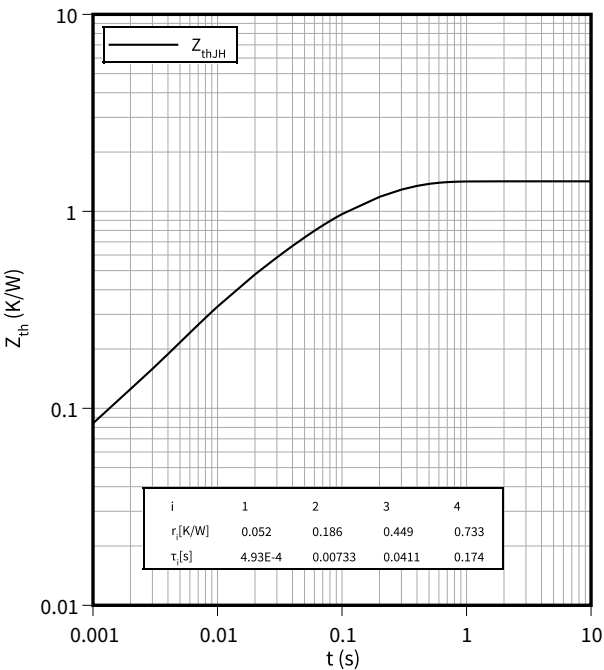
Reverse bias safe operating area (RBSOA), IGBT, Boost

$I_C = f(V_{CE})$
 $T_{vj} = 150\text{ }^{\circ}\text{C}$, $R_{Goff} = 18\text{ }\Omega$, $V_{GE} = \pm 15\text{ V}$



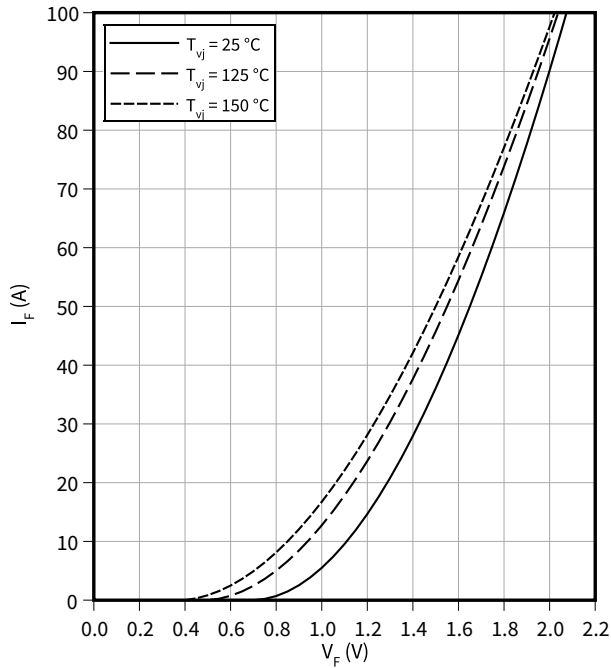
Transient thermal impedance, IGBT, Boost

$Z_{th} = f(t)$



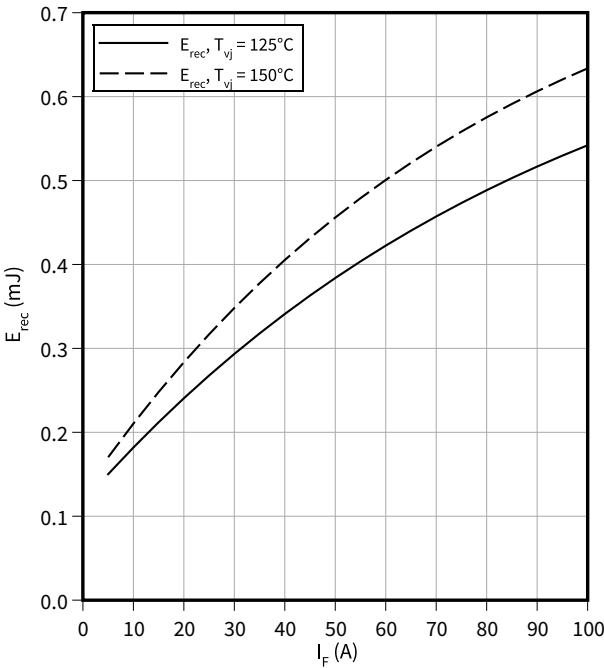
Forward characteristic (typical), Diode, Boost

$I_F = f(V_F)$



Switching losses (typical), Diode, Boost

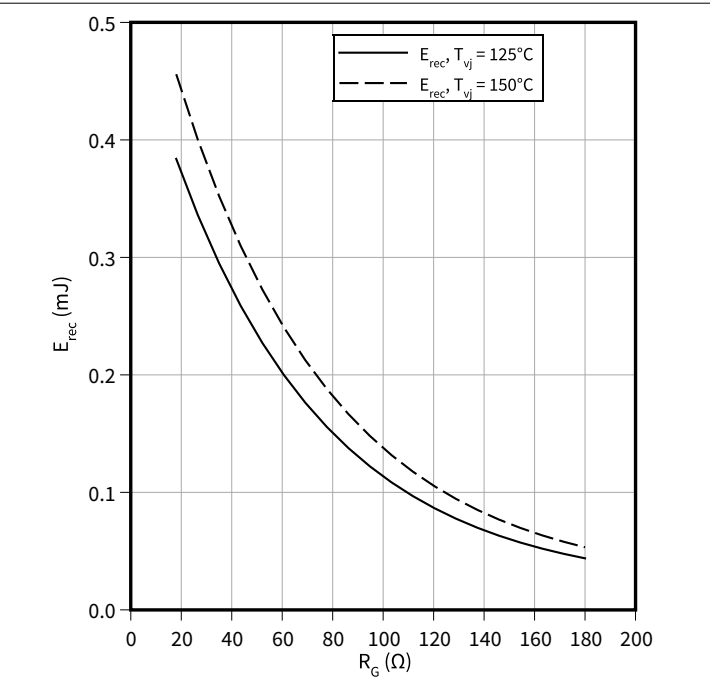
$E_{rec} = f(I_F)$
 $R_{Gon} = R_{Gon}(IGBT)$, $V_{CC} = 300\text{ V}$



9 Characteristics diagrams

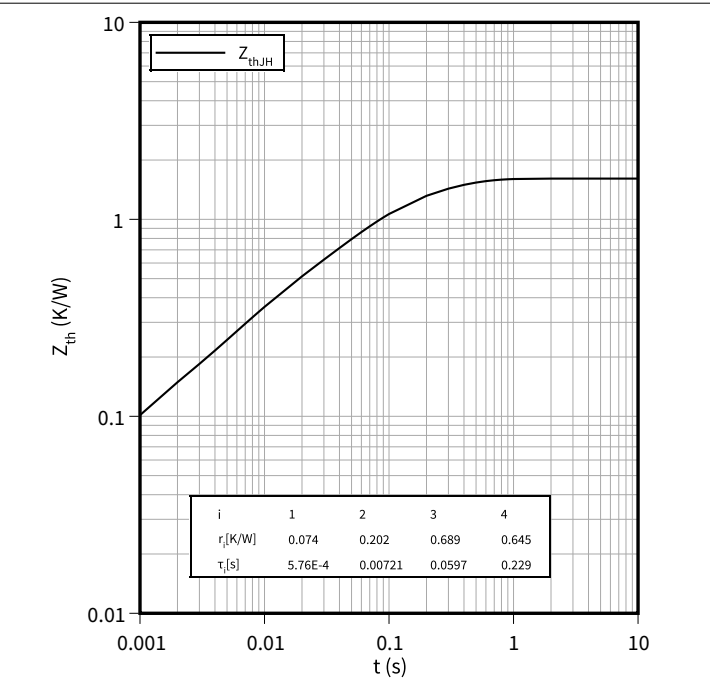
Switching losses (typical), Diode, Boost

$E_{rec} = f(R_G)$
 $I_F = 50\text{ A}, V_{CC} = 300\text{ V}$



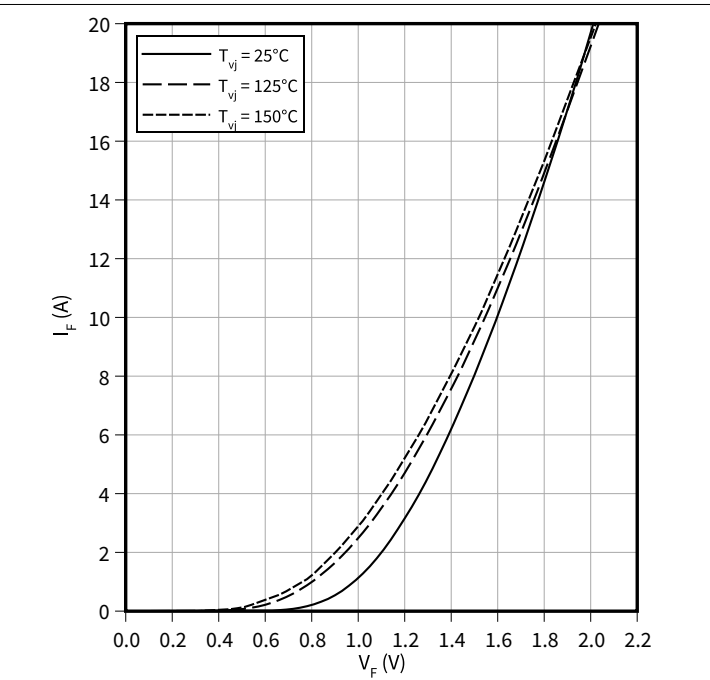
Transient thermal impedance, Diode, Boost

$Z_{th} = f(t)$



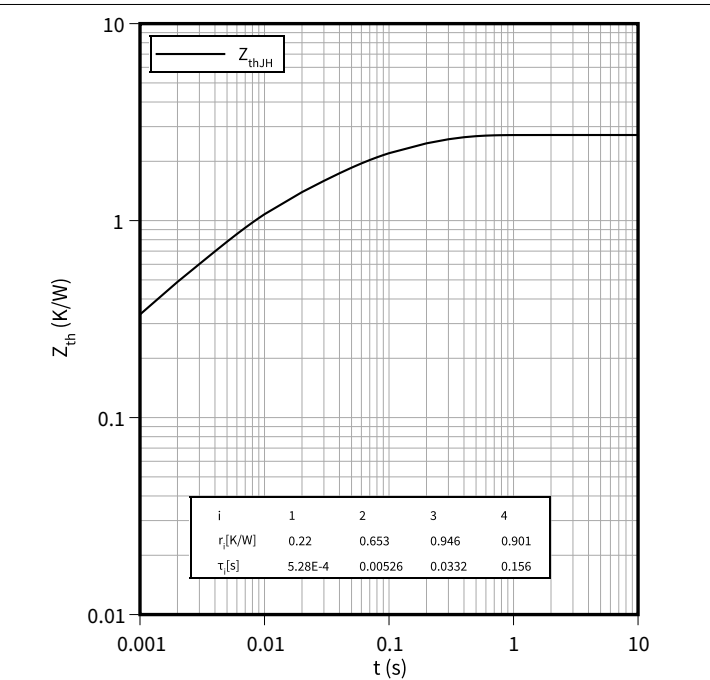
Forward characteristic (typical), Diode, Reverse

$I_F = f(V_F)$



Transient thermal impedance, Diode, Reverse

$Z_{th} = f(t)$



10 Circuit diagram

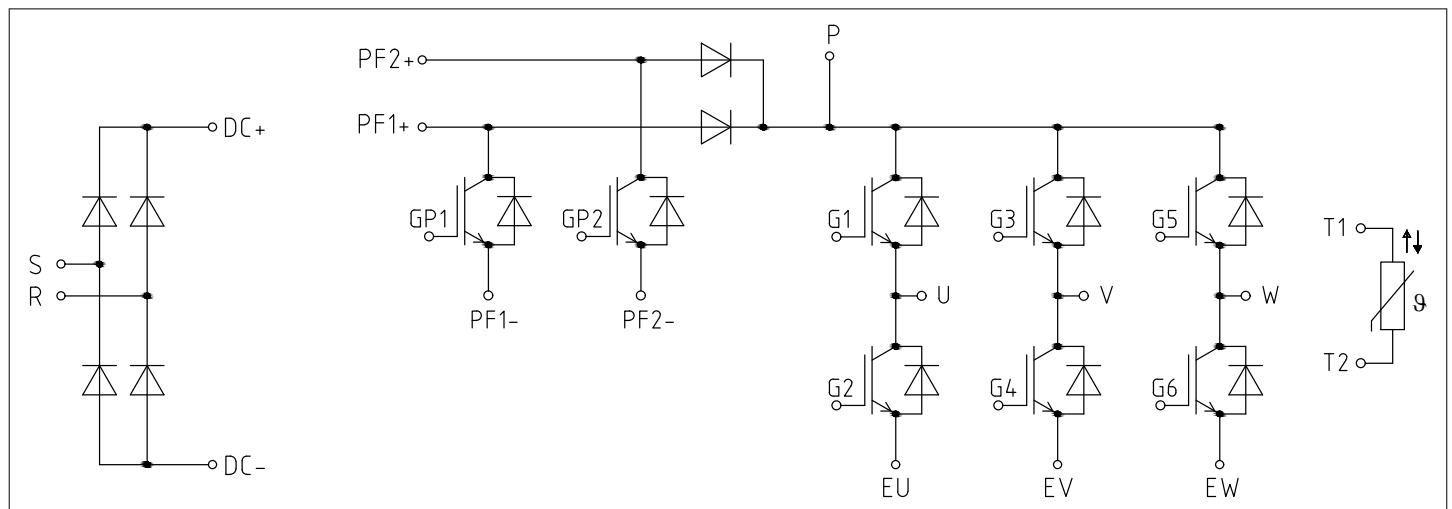


Figure 1

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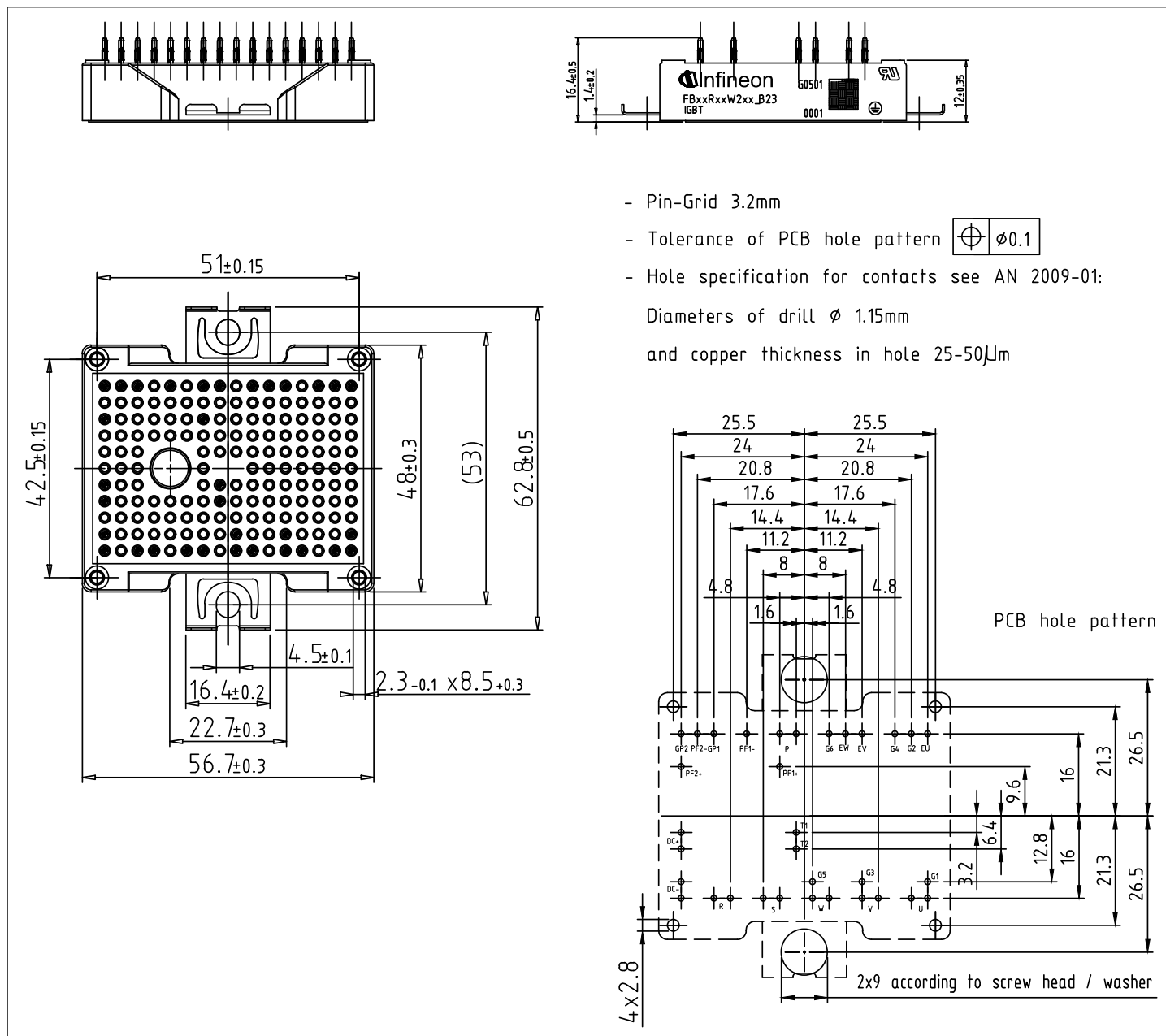


Figure 2

12 Module label code

Module label code			
Code format	Data Matrix		Barcode Code128
Encoding	ASCII text		Code Set A
Symbol size	16x16		23 digits
Standard	IEC24720 and IEC16022		IEC8859-1
Code content	<i>Content</i>	<i>Digit</i>	<i>Example</i>
	Module serial number	1 – 5	71549
	Module material number	6 - 11	142846
	Production order number	12 - 19	55054991
	Date code (production year)	20 – 21	15
	Date code (production week)	22 – 23	30
Example			
			
71549142846550549911530		71549142846550549911530	

Figure 3

Revision history

Document revision	Date of release	Description of changes
V1.0	2019-06-24	Target datasheet
V1.1	2020-03-20	Target datasheet
n/a	2020-09-01	Datasheet migrated to a new system with a new layout and new revision number schema: target or preliminary datasheet = 0.xy; final datasheet = 1.xy
1.00	2021-03-25	
1.01	2022-09-16	Correction according ERRATA 10282ERRA

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Edition 2022-09-16

Published by

Infineon Technologies AG
81726 Munich, Germany

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Document reference
IFX-AAY200-004

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